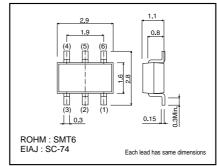
# Power management (dual digital transistors) IMD10A

#### Features

- 1) Two digital class transistors in a SMT package.
- 2) Up to 500mA can be driven.
- Low Vce(sat) of drive transistors for low power dissipation.

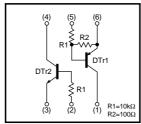
## ●Dimensions (Unit:mm)



# ●Package, marking, and packaging specifications

| Part No.                     | IMD10A |
|------------------------------|--------|
| Package                      | SMT6   |
| Marking                      | D10    |
| Code                         | T108   |
| Basic ordering unit (pieces) | 3000   |

## ●Equivalent circuit



# ● Absolute maximum ratings (Ta=25°C)

# DTr<sub>1</sub>

| Parameter         | Symbol | Limits   | Unit |
|-------------------|--------|----------|------|
| Supply voltage    | Vcc    | -50      | V    |
| Input voltage     | Vin    | −5 to +5 | V    |
| Collector current | Ic     | -500     | mA   |

#### DTr<sub>2</sub>

| Parameter                 | Symbol | Limits | Unit |
|---------------------------|--------|--------|------|
| Collector-base voltage    | Vсво   | 50     | V    |
| Collector-emitter voltage | VCEO   | 50     | V    |
| Emitter-base voltage      | VEBO   | 5      | V    |
| Collector current         | Ic     | 100    | mA   |

#### Total

| Parameter            | Symbol | Limits      | Unit |  |
|----------------------|--------|-------------|------|--|
| Power dissipation    | Pd     | 300(TOTAL)  | mW * |  |
| Junction temperature | Tj     | 150         | °C   |  |
| Storage temperature  | Tstg   | -55 to +150 | °C   |  |

<sup>\* 200</sup>mW per element must not be exceeded.

# ●Electrical characteristics (Ta=25°C)

#### DTr<sub>1</sub>

| Parameter            | Symbol              | Min. | Тур. | Max.                  | Unit | Conditions                       |
|----------------------|---------------------|------|------|-----------------------|------|----------------------------------|
| Land callens         | V <sub>I(off)</sub> | -0.3 | V    | Vcc= -5V , Io= -100μA |      |                                  |
| Input voltage        | V <sub>I(on)</sub>  | -1.5 | _    | _                     | V    | Vo= -0.3V , Io= -100mA           |
| Output voltage       | V <sub>O(on)</sub>  | _    | -0.1 | -0.3                  | V    | lo= -100mA , l≔ -5mA             |
| Input current        | lı                  | _    | _    | -25                   | mA   | V₁= <b>-</b> 2V                  |
| Output current       | IO(off)             | _    | _    | -0.5                  | μΑ   | Vcc= -50V , Vi=0V                |
| DC current gain      | Gı                  | 68   | _    | _                     | _    | lo= -100mA , Vo= -5V             |
| Transition frequency | f⊤                  | _    | 200  | _                     | MHz  | Vc== -10V , I==50mA , f=100MHz * |
| Input resistance     | R <sub>1</sub>      | 70   | 100  | 130                   | Ω    | _                                |
| Resistance ratio     | R2 / R1             | 80   | 100  | 120                   | _    | _                                |

<sup>\*</sup> Transition frequency of the device.

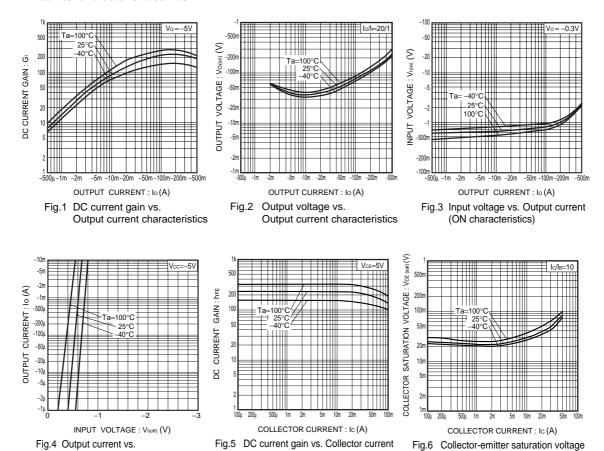
#### DTr<sub>2</sub>

| Parameter                            | Symbol         | Min. | Тур. | Max. | Unit | Conditions                    |
|--------------------------------------|----------------|------|------|------|------|-------------------------------|
| Collector-base breakdown voltage     | ВУсво          | 50   | _    | _    | V    | Ic=50μA                       |
| Collector-emitter breakdown voltage  | BVceo          | 50   | _    | _    | V    | Ic=1mA                        |
| Emitter-base breakdown voltage       | ВVево          | 5    | _    | _    | V    | Iε=50μA                       |
| Collector cutoff current             | Ісво           | _    | _    | 0.5  | μΑ   | Vcb=50V                       |
| Emitter cutoff current               | ІЕВО           | _    | _    | 0.5  | μΑ   | V <sub>EB</sub> =4V           |
| Collector-emitter saturation voltage | VCE(sat)       | _    | _    | 0.3  | V    | Ic=10mA , I <sub>B</sub> =1mA |
| DC current transfer ratio            | hfe            | 100  | 250  | 600  | _    | VcE=5V , Ic=1mA               |
| Transition frequency                 | f⊤             | _    | 250  | _    | MHz  | Vc=10V , I=-5mA , f=100MHz *  |
| Input resistance                     | R <sub>1</sub> | 7    | 10   | 13   | kΩ   | _                             |

 $<sup>\*</sup>$  Transition frequency of the device.

#### •Electrical characteristic curves

Input voltage (OFF characteristics)



vs. Collector current

Rev.B

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